MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

MJD41C(MS)

Product specification





SEMICONDOCTOR -

ISKSEMI

TRANSISTOR (NPN)

FEATURES

- Designed for General Purpose Amplifier and Low Speed S witching Applications.
- Lead Formed for Surface Mount Applications in Plastic Sleeves
- Electrically Similar to Popular TIP41 and TIP42 Series
- Monolithic Construction With Built-in Base-Emitter Resistors

Reference News

PACKAGE	OUTLINE	COMPLEMENTARY	Marking
	1.BASE 2.COLLECTOR 3.EMITTER	COLLECTOR 1 BASE 3 EMITTER	MSKSEMI MJD41C MS XXX

Notes :XXX represents the order code.

MAXIMUM RATINGS (Ta=25 ℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
Vсво	Collector-Base Voltage	100	V
V _{CEO}	Collector-EmitterVoltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current -Continuous	6	А
ICP*	Collector Current -Pluse	10	А
Pc	Collector Power Dissipation	1.25	W
T _{J,} T _{stg}	Operating Junction and Storage Temperature Range	-55-150	°C



ELECTRICAL CHARACTERISTICS (T₄=25℃ unless otherwise specified)

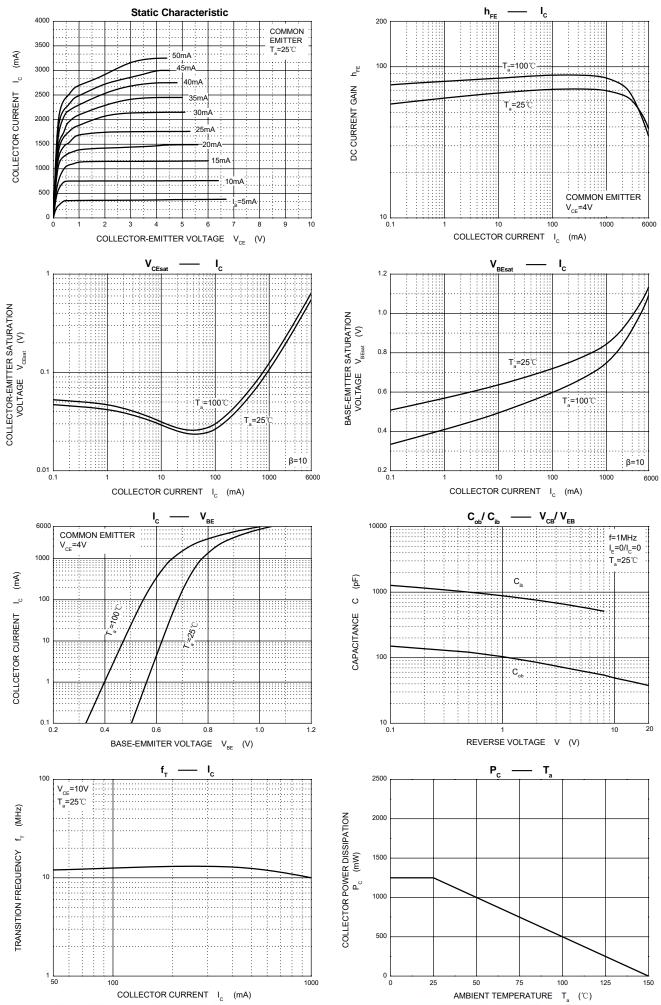
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	lc=100μΑ,I _E =0	100			V
Collector-emitter breakdown voltage	V _{CEO(sus)}	Ic=30mA,I _B =0	100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	l _E =100μA,I _C =0	5			V
Collector cut-off current	ICEO	V _{CB} =60V,I _E =0			50	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V I _C =0			0.5	mA
DC current acia	h _{FE(1)}	V _{CE} =4V I _C =0.3A	30			
DC current gain	h _{FE(2)}	V _{CE} =4V,I _C =3A	15		75	
Collector-emitter saturation voltage	V _{CE(sat)}	lc=6A,I _B =0.6A			1.5	V
Base-emitter voltage	V _{BE}	V _{CE} =4V,I _C =6A			2	V
Transition frequency	f⊤	V _{CE} =10V,I _C =500mA,f=1MHz	3			MHz

* Pulse Test: PW≤300µs, Duty Cycle≤2%



MJD41C(MS)

Typical Characteristics



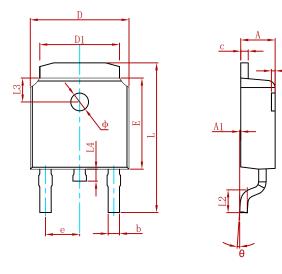
Copyright© Msksemi Incorporated

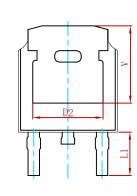
Downloaded From Oneyac.com

<u>www.msksemi.com</u>



PACKAGE MECHANICAL DATA

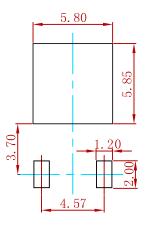




Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063	REF.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207	REF.	

h

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MJD41C(MS)	TO-252	2500



Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.

Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or

mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to

product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)